



Resonant tunneling through quantum well at frequencies up to 2.5 THz

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Abstract

Resonant tunneling through a single quantum well of GaAs has been observed. The current singularity and negative resistance region are dramatically improved over previous results, and detecting and mixing have been carried out at frequencies as high as 2.5 THz. Resonant tunneling features are visible in the conductance-voltage curve at room temperature and become quite pronounced in the *I-V* curves at low temperature. The high-frequency results, measured with far IR lasers, prove that the charge transport is faster than about 10^{-13} s. It may now be possible to construct practical nonlinear devices using quantum wells at millimeter and submillimeter wavelengths.

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